

**Amended claims:**

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**A 1**  
2. (Once Amended) A method of increasing the holding voltage of a LVTSCR structure, comprising forming at least one additional p-region and n-region inside a p-well of the structure to define a p-n junction that is forward biased during normal operation.

3. (Once Amended) A method of increasing the holding voltage of a LVTSCR-like structure having an anode and a cathode, comprising providing an alternative current path from anode to cathode through a p-well of the structure, other than purely the current path from anode to cathode through the p-material of the p-well.

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**A 2**  
5. (Once Amended) A method of claim 4, wherein the lower resistance current path takes the form of at least one p-n junction that is forward biased under normal operating conditions, formed in the p-well.

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